

Supporting Information (SI)

Multifunctioning Graphene Oxide Capping Layer for Highly Efficient and Stable PEDOT:PSS-Silicon Hybrid Solar Cells

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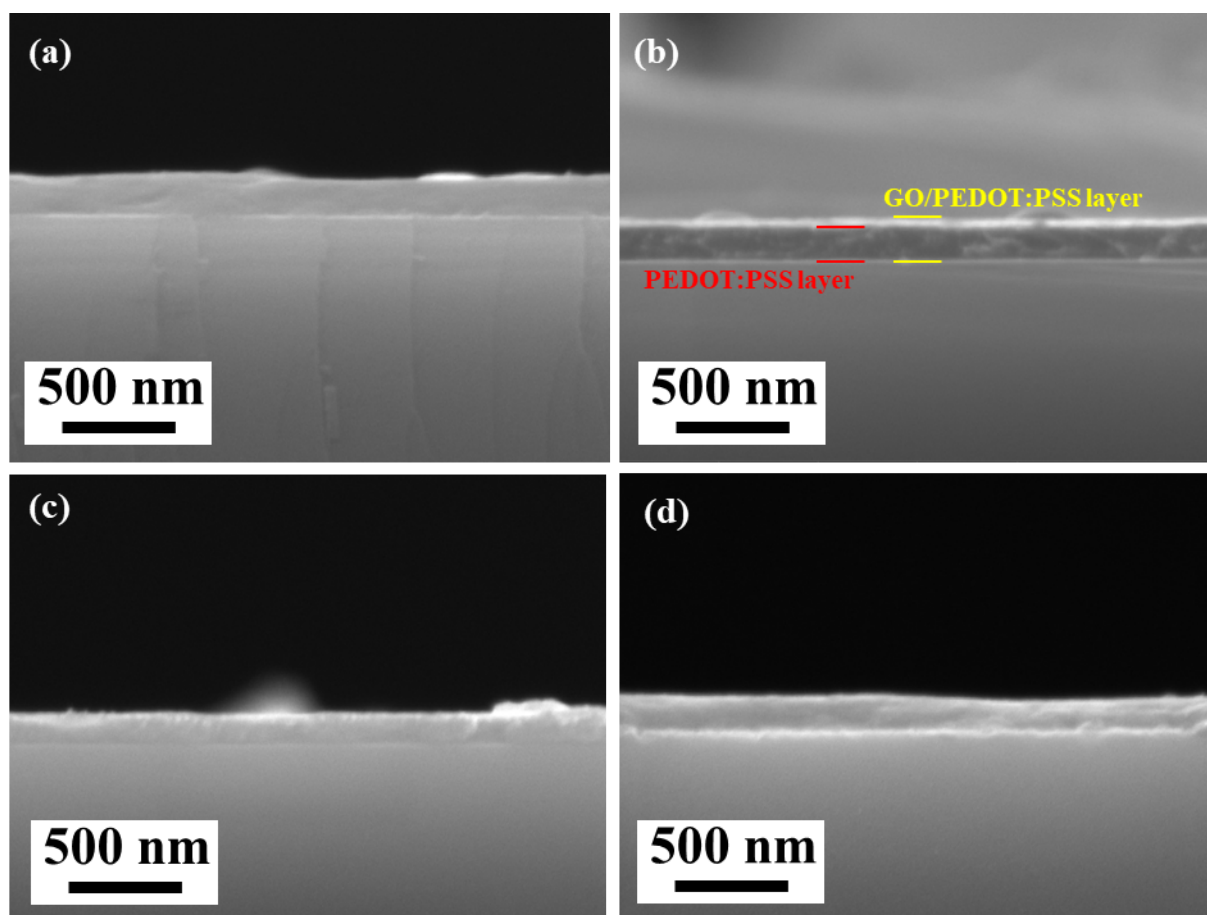


Figure S1. FESEM images for (a) only PEDOT:PSS layer and GO/PEDOT:PSS dual layer of, (b) PIGO2, (c) PIGO4, (d) PIGO6 over mirror polished Si wafers.

Table S1: Comparison of photovoltaic characteristics of the prior works for PEDOT:PSS/Si solar cells with the present work.

Device Structure and Dimensions	Properties of Si wafers used	PEDOT:PSS and additive (as secondary dopants, surfactant, etc.)	Advanced structuring and processing	Remarks	Performance parameters of HHSCs				Reference No; Year
					J_{sc} (mA/cm ²)	V_{oc} (V)	FF (%)	PCE (%)	
Au/PEDOT:PSS/textured n-Si/In:Ga (1.1×1.1 cm ²)	n-type (100) (ρ: 1-10 Ω-cm) (t: 500 ± 20 μm)	DMSO (5 wt%) Zonyl fluorosurfactant (0.15 wt%)	Glove box has been used	KOH based alkyl etching	24.58	0.515	40.43	5.17	1; 2022
Ag/PEDOT:PSS/GO-AuNPs/n-Si/Ti/Ag	-	PEDOT:PSS/GO-AuNPs			26.23	0.525	61	8.39	2 2022
Al/PEDOT:PSS/AgNPs//SiNWs/ITO/Glass (2.25 cm ²)	n-type, (t: 530 μm) (ρ: 15 Ω-cm)	DMSO (5 wt%) Triton X: (1%)	Ag NPs on SiNWs		24.95	0.54	66.53	8.96	3; 2020
Ag/HQ-PEDOT:PSS/BQ/n-Si/LiF/Al (2×2 cm ²)	n-Si (100) (ρ: 1.7-2.3 Ω-cm) (t: 280 μm)	Hydroquinone (HQ)-Modified+ DMSO, Triton X-100	Benzoquinone (BQ)	Solution processed	27.7	0.618	61.8	10.6	4; 2022
Cr/Au/PEDOT:PSS/VGNH/Al ₂ O ₃ /n-Si/Ti/Pd/Ag (0.30 cm ²)	n-type (<100> P doped) (ρ: 1-5 Ω-cm) (t : 500 μm)	IPA for dilution, HNO ₃ doping	graphene nano hills (VGNH)/Al ₂ O ₃ passivation	Pyramid textured	34.99	0.560	56.01	10.97	5; 2020
Ag/GO/PEDOT:PSS/n-Si/In:Ga (1.5.×1.5 cm²)	Solar grade, as-cut Si wafers n-type (100) (CZ) (ρ: 1-3 Ω-cm) (t: 180±20 μm)	EG (7 wt%) + IPA	GO as capping layer over PEDOT:PSS	Pyramid texturing	29.79	0.560	69.90	11.66	Present work
Ti/Ag/PEDOT:PSS/n c-Si/i a-Si:H /n a-Si:H/PEDOT:PSS/Al (1 × 1 cm ²)	n-type (100) (CZ) (ρ: 1-3 Ω-cm) t:150 μm	PEDOT:PSS DMSO (5 wt%) Triton X-100 (0.5%)	i-a-Si:H /n-a-Si:H	PECVD	29.7	0.620	65.8	12.1	6; 2016
Ag/PEDOT:PSS/Si/Ag	n-type, radial <100> ±	EG (5 wt %)	Annealing in		29.19	0.579	73.08	12.35	7;

(1×1cm ²)	0.5°, single-side polished (ρ: 2-4 Ω-cm) (t : 400 μm)	TX-100 (0.25 wt%)	muffle furnace at 120 °C							2021
Ag/PEDOT:PSS/Si/Ag (0.5×0.5 cm ²)	n-Si, radial (100), polished single side, (ρ: 2-4 Ω-cm) (t : 500 μm)	EG (5 wt %) TX-100 (0.25 wt%)	TX-100: 0.25 magnetic stirring for 8 h,		30.81	0.560	71	12.38		8; 2021
Ag/PEDOT:PSS/Rubrene/n -Si/Ag (0.5 × 0.5cm ²)	n-Si (polished single- side, radial (100) (ρ: 2-4 Ω-cm) (t: 500 μm)	EG (5 wt %) TX-100 (0.25 wt%)	rubrene EG suspension interface		28.83	0.586	74.5	12.59		9; 2021
Ag/PMMA/Graphene/PED OT:PSS/SiO ₂ / Si/In-Ga (1.2 × 1.2 cm ²)	n-type (100) (ρ: 1-10 Ω-cm) (t: 500 μm) 300 nm thick oxide layer	(DMSO) (5 wt%) (IPA) Triton X-100 (1 wt%)	CH ₃ - terminated surface	Chlorinatio n, methylation in glove box	30.63	0.580	73	13.01		10; 2022
Ag/ PEDOT:PSS-V ₂ O ₅ /n- Si/Al (0.8 cm ²)	n-type [100], (ρ: 0.05-0.10 Ω-cm) (t: 290 ± 10 μm)	PEDOT:PSS-V ₂ O ₅ composite	glove box filled with nitrogen gas		32.80	0.652	70.98	15.17		11; 2023
AgNW/Ag grid/ PEDOT:PSS/ Siloxane/μT- Si/Siloxane/Ti/Ag (1 cm ²)	CZ c-Si Both side polished (ρ:1-5 Ω cm) t=250 μm	Methanol (78.5 wt%) EG (1.5 wt %)	Siloxane	Contact printing (70 °C, 3h)	38.09	0.620	74.58	17.61		12; 2019

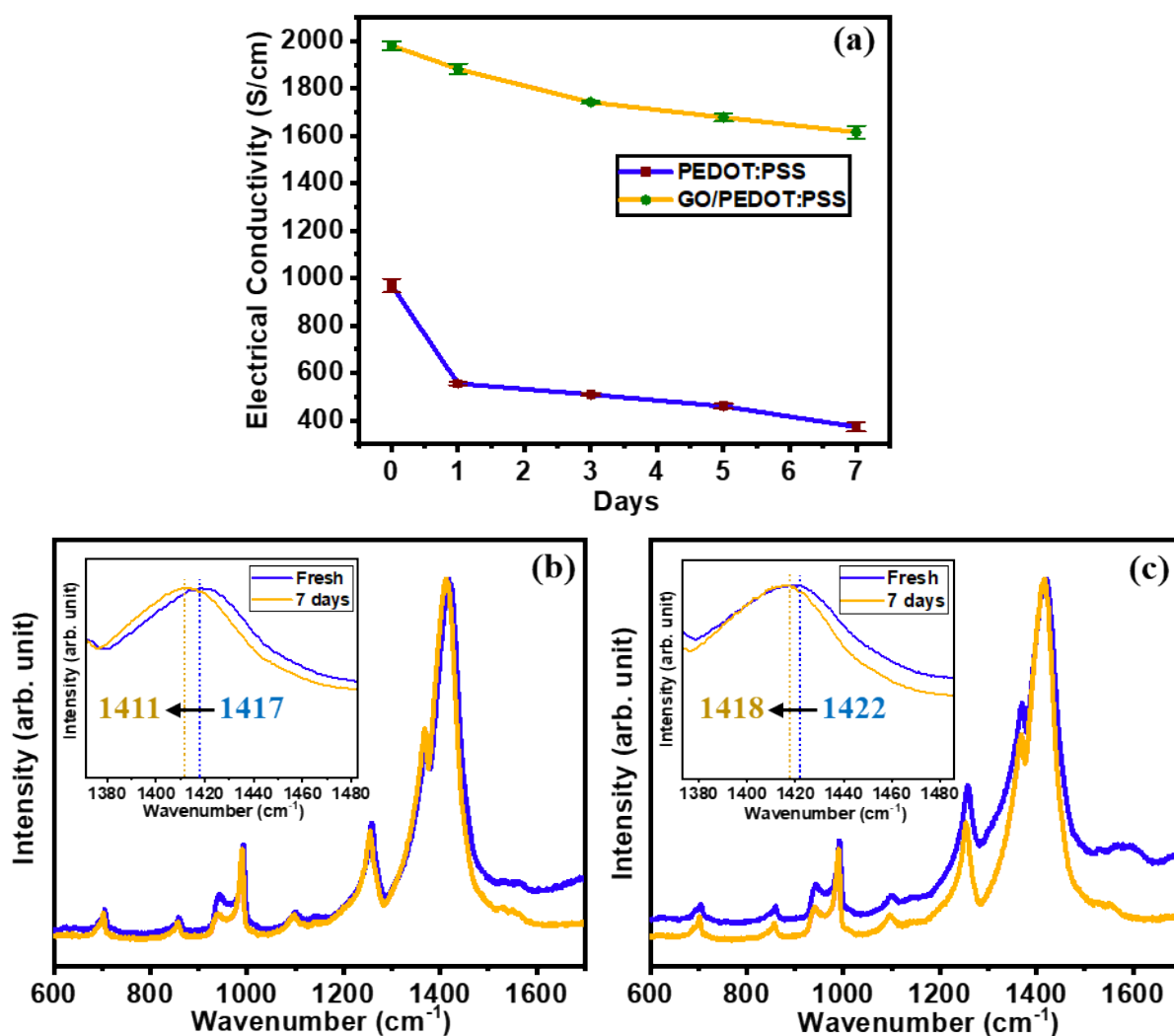


Figure S2. (a) Electrical conductivity and Raman spectroscopy results for the (b) PEDOT:PSS and, (c) GO/PEDOT:PSS layers over 7 days of aging time under atmospheric conditions.

References

- [1] C. Li, Z. He, Q. Wang, J. Liu, S. Li, X. Chen, W. Ma, Y. Chang, *Silicon*, 2022, **14**, 2299-2307.
- [2] N. V. Tu, N. N. Anh, T. V. Hau, N. V. Hao, N. T. Huyen, B. H. Thang, P. N. Minh, N. V. Chuc, N. Fukata, P. V. Trinh, *RSC Adv.*, 2022, **12**, 27625.
- [3] E. Jbira, H. Derouiche, K. Missaoui, *Sol. Energy*, 2020, **211**, 1230-1238
- [4] N.Y. Park, G.S. Jeong, Y.-J. Yu, Y.-C. Jung, J.H. Lee, J.H. Seo, J.-Y. Choi, *Polymers* 2022, **14**, 478.
- [5] M. A. Rehman, S. B. Roy, D. Gwak, I. Akhtar, N. Nasir, S. Kumar, M. F. Khan, K. Heo, S.-H. Chun, Y. Seo, *Carbon*, 2020, **164**, 235-243.
- [6] X. Zhang, D. Yang, Z. Yang, X. Guo, B. Liu, X. Ren, S. Liu, *Sci. Rep.* 2016, **6**, 35091.
- [7] Z. Gao, T. Gao, Q. Geng, G. Lin, Y. Li, L. Chen, M. Li, *Sol. Energy*, 2021, **228**, 299-307.

- [8] Q. Geng, Z. Wang, Z. Gao, T. Gao, Y. Li, L. Chen, M. Li, *J. Phys. Chem. C* 2021, **125**, 26379-26388.
- [9] T. Gao, Q. Geng, Z. Gao, Y. Li, L. Chen, M. Li, *ACS Appl. Energy Mater.*, 2021, **4**, 12543-12551.
- [10] P. Xiao, M. Zhang, X. Wu, K. Ding, J. Pan, J. Jie, *Sol. Energy* 2022, **234**, 111-118.
- [11] Z. Luo, C. Yang, X. Chen, W. Ma, S. Li, K. Fu, *J. Materiomics.*, 2023, **9**, 438-446.
- [12] S-S. Yoon, D.-Y. Khang, *J. Phys. Chem. Solids*, 2019, **129**, 128-132.